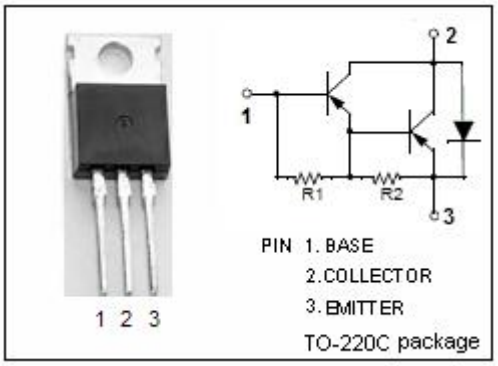
isc Silicon PNP Darlington Power Transistor 2SB1286

DESCRIPTION

- High DC Current Gain-
  :h_{FE} = 1000(Min)@ I_C= -1A
- Collector-Emitter Breakdown Voltage-
  :$V_{(BR)CEO}$ = -100V(Min)
- Low Collector-Emitter Saturation Voltage
  :$V_{CE(sat)}$ = -1.5V(Max)@ I_C= -1A
- Complement to Type 2SD1646
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

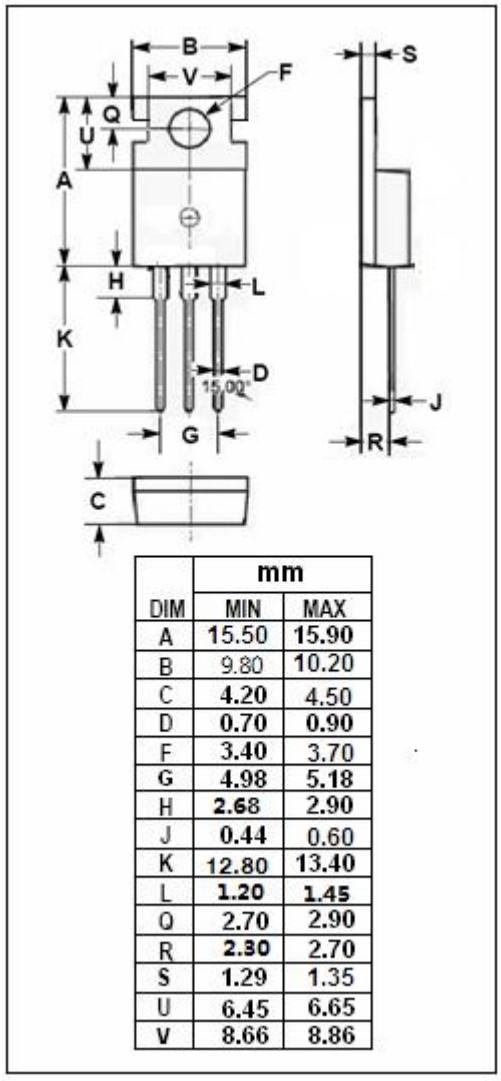


APPLICATIONS

- Designed for general purpose amplifier and low speed switching applications.

ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-3	A
P_C	Collector Power Dissipation T_C=25℃	25	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -5mA, I_B= 0	-100			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -50 μA, I_E= 0	-100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B= -1mA			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V; I_E= 0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -7V; I_C= 0			-3	mA
h_{FE}	DC Current Gain	I_C= -1A; V_{CE}= -2V	1000		10000	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V; f= 1MHz		35		pF